

Reference 3: Japanese Patent Application Laid Open No. 2000-292908

Title of the Invention: Pellicle for Photolithography

Filing Date: April 2, 1999

Applicant: Shin-Etsu Chemical Co., Ltd.

Extract:

See US Patent No. 6368683.

PATENT ABSTRACTS OF JAPAN

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(71)Applicant : SHIN ETSU CHEM CO LTD

(22)Date of filing : 02.04.1999

(72)Inventor : SHIRASAKI SUSUMU

(54) PELLICLE FOR LITHOGRAPHY

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a pellicle for lithography consisting of a pellicle film which has high transmittance of light and excellent durability even when the film is irradiated with vacuum UV rays of short wavelengths for a long time.

SOLUTION: This pellicle for lithography consists of at least a pellicle film adhered to a pellicle frame, and the pellicle film used has $\geq 50\%$ transmittance of light when the film is irradiated with excimer laser light of ≤ 160 nm. The material of the pellicle film is an inorg. fluoride, and the inorg. fluoride is calcium fluoride or magnesium fluoride.

LEGAL STATUS

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Reference 4: Japanese Patent Application Laid Open No. H10-92743

Title of the Invention: X-Ray Mask Pellicle

Filing Date: September 1, 1997

Priority Date: September 6, 1996

Applicant: International Business Machines Corporation

Extract:

See US Patent No. 5793836.